

Alexander Hardtdegen

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Cation diffusion in polycrystalline thin films of monoclinic HfO ₂ deposited by atomic layer deposition. APL Materials, 2020, 8, .	5.1	7
2	Variability-Aware Modeling of Filamentary Oxide-Based Bipolar Resistive Switching Cells Using SPICE Level Compact Models. IEEE Transactions on Circuits and Systems I: Regular Papers, 2020, 67, 4618-4630.	5.4	72
3	Evolution of short-range order in chemically and physically grown thin film bilayer structures for electronic applications. Nanoscale, 2020, 12, 13103-13112.	5.6	13
4	Vertical Ge Gate-All-Around Nanowire pMOSFETs With a Diameter Down to 20 nm. IEEE Electron Device Letters, 2020, 41, 533-536.	3.9	13
5	Exploiting the switching dynamics of HfO ₂ -based ReRAM devices for reliable analog memristive behavior. APL Materials, 2019, 7, .	5.1	94
6	KMC Simulation of the Electroforming, Set and Reset Processes in Redox-Based Resistive Switching Devices. IEEE Nanotechnology Magazine, 2018, 17, 1181-1188.	2.0	21
7	Improved Switching Stability and the Effect of an Internal Series Resistor in HfO ₂ /TiO ₂ Bilayer ReRAM Cells. IEEE Transactions on Electron Devices, 2018, 65, 3229-3236.	3.0	95
8	Tuning the Performance of Pt/HfO ₂ /Ti/Pt ReRAM Devices Obtained from Plasma-Enhanced Atomic Layer Deposition for HfO ₂ Thin Films. ECS Transactions, 2016, 75, 177-184.	0.5	18
9	Internal Cell Resistance as the Origin of Abrupt Reset Behavior in HfO ₂ -Based Devices Determined from Current Compliance Series. , 2016, , .		13